MMBTA55

Rev.F Apr.-2017

DATA SHEET

/ Descriptions

Silicon PNP transistor in a SOT-23 Plastic Package.

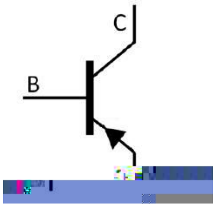
/ Features

Complementary to MMBTA05.

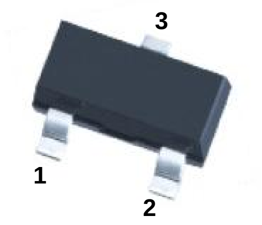
/ Applications

Ideal for medium power amplification and switching.

/ Equivalent Circuit



/ Pinning



PIN1 Base PIN 2 Emitter PIN 3 Collector

/ h_{FE} Classifications & Marking

h_{FE} Range	100 300
Marking	H2H

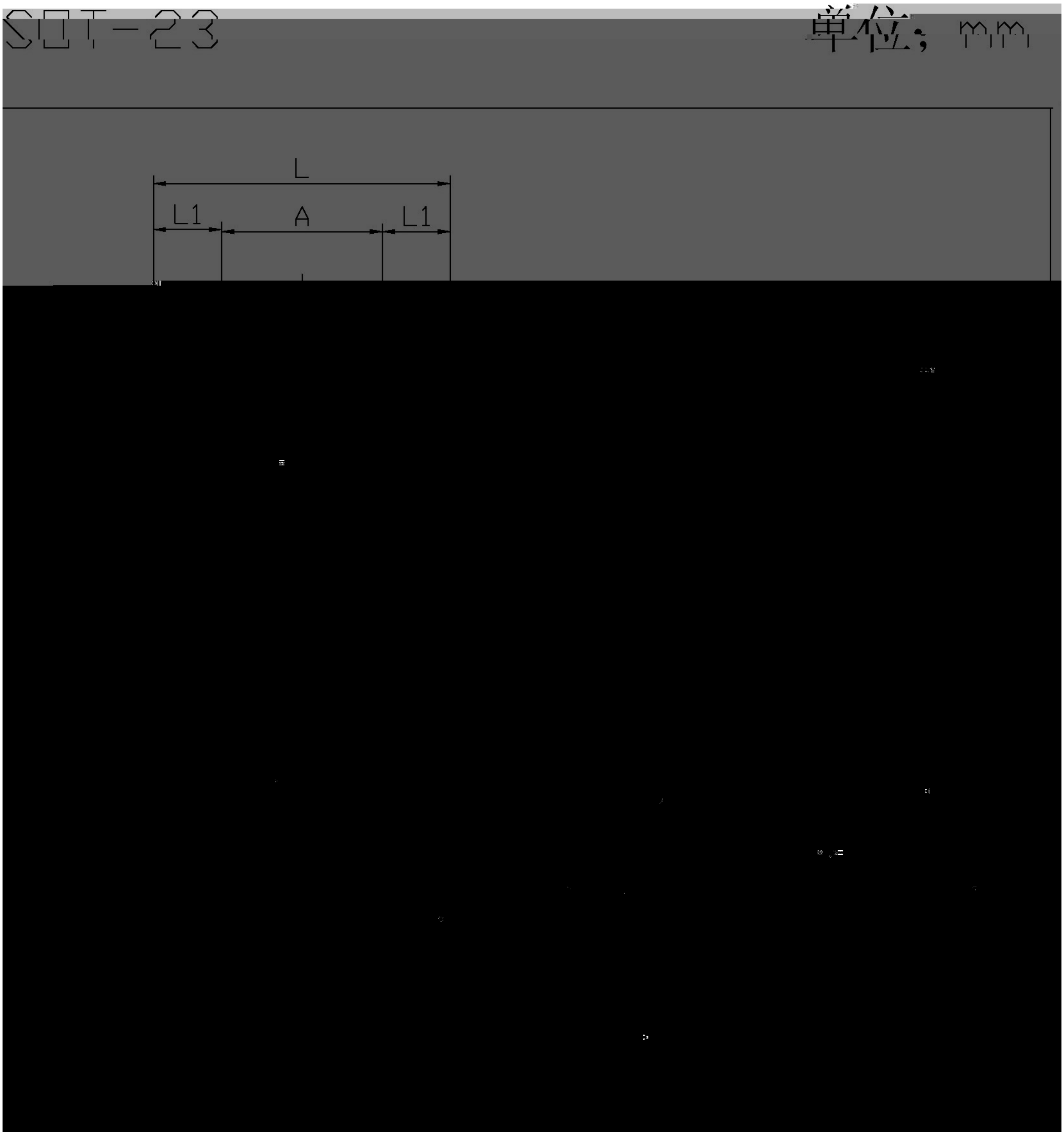
Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	-60	V
Collector to Emitter Voltage	V_{CEO}	-60	V
Emitter to Base Voltage	V_{EBO}	-4.0	V
Collector Current	I_C	-500	mA
Collector Power Dissipation	P_D	300	mW
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector to Base Breakdown Voltage	V_{CBO}	I_C=-100 A I_E=0	-60			V
Collector to Emitter Breakdown Voltage	V_{CEO}	I_C=-1.0mA I_B=0	-60			V
Emitter to Base Breakdown Voltage	V_{EBO}	I_E=-100 A I_C=0	-4.0			V
Collector Cut-Off Current	I_{CBO}	V_{CB}=-60V I_E=0			-0.1	A

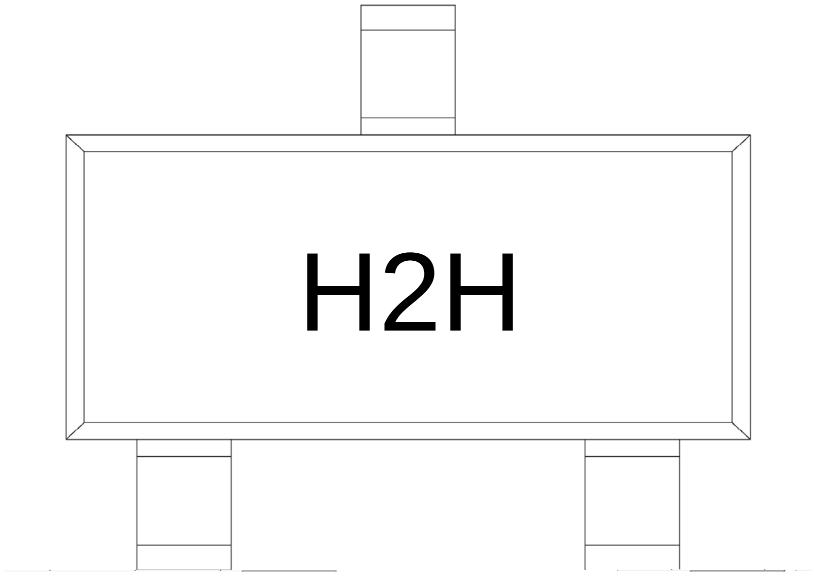
Collector Emitter Cutoff Current   I   V

/ Electrical Characteristic Curve

/ Package Dimensions



/ Marking Instructions

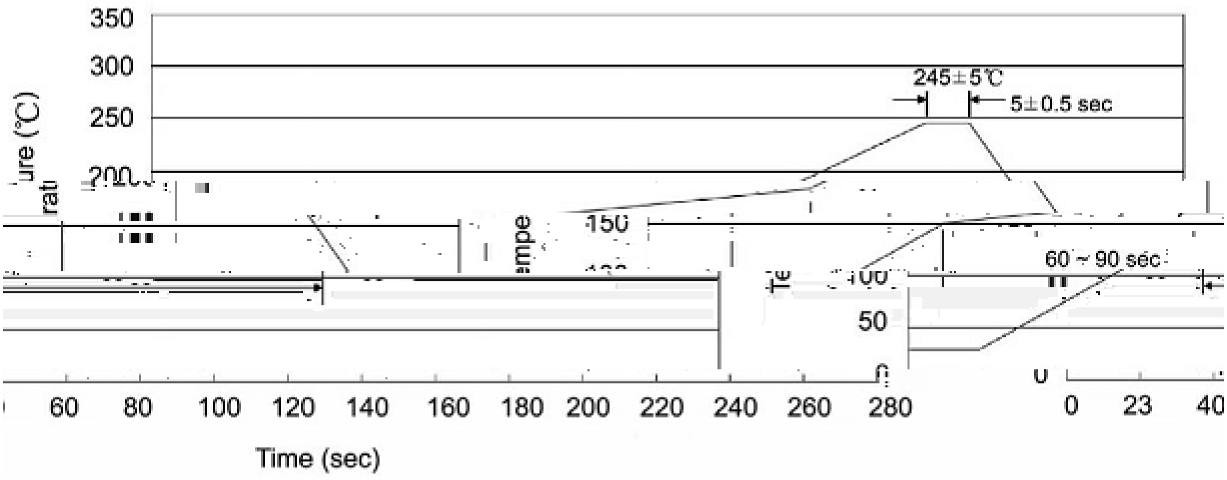


Note:

Company Code

Product Type

( ) / Temperature Profile for IR Reflow Soldering(Pb-Free)



1 25 150 60 90sec;
2 245 5 5 0.5sec;
3 2 10 /sec.

Note:
1.Preheating:25~150 , Time:60~90sec.
2.Peak Temp.:245 5 , Duration:5 0.5sec.
3. Cooling Speed: 2~10 /sec.

/ Resistance to Soldering Heat Test Conditions

260 5 10 1 sec.

Temp.:260±5 Time:10±1 sec

/ Packaging SPEC.

/ REEL

Package Type	Units					Dimension (unit mm^3)		
	Units/Reel /	Reels/Inner Box /	Units/Inner Box /	Inner Boxes/Outer Box /	Units/Outer Box /	Reel	Inner Box	Outer Box
SOT-23	3,000	10	30,000	6	180,000	7 ×8	180×120×180	390×385×205

/ Notices